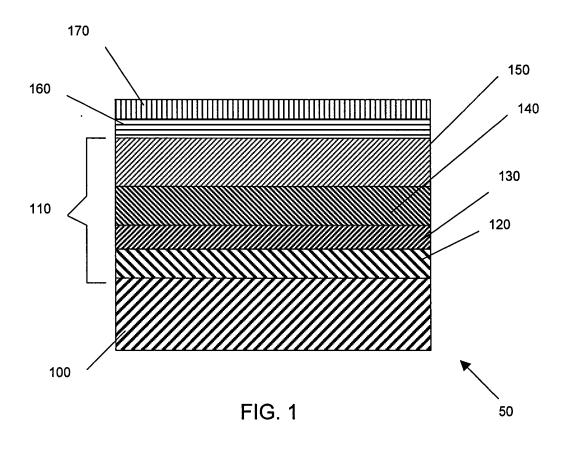
Title: SEMICONDUCTOR HETEROSTRUCTURES HAVING REDUCED DISLOCATION PILE-UPS AND

RELATED METHODS Inventors: Leitz et al.

Express Mail Label No. EV192308504US
Atty Docket No.: ASC-058B
Attorney for Applicants: Mark L. Beloborodov
Sheet 1 of 6



HAVING REDUCED DISLOCATION PILE-UPS AND RELATED METHODS
Inventors: Leitz et al.
Express Mail Label No. EV192308504US
Atty Docket No.: ASC-058B
Attorney for Applicants: Mark L. Beloborodov
Sheet 2 of 6

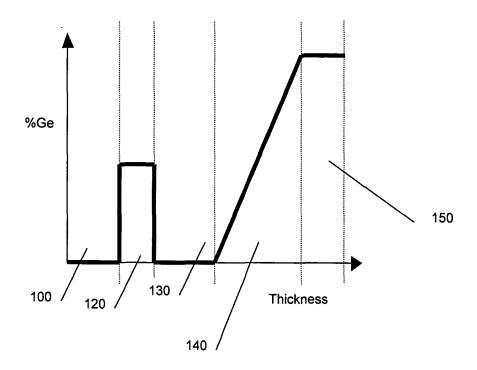


FIG. 2

HAVING REDUCED DISLOCATION PILE-UPS AND RELATED METHODS
Inventors: Leitz et al.
Express Mail Label No. EV192308504US
Atty Docket No.: ASC-058B
Attorney for Applicants: Mark L. Beloborodov
Sheet 3 of 6

	Qualitative Evaluation of Dislocation Pile-Up Density			
% Ge	$H^* = 0.6 T_{crit}$	$H = 1.25 T_{crit}$	$H = 2 T_{crit}$	$H = 5 T_{crit}$
5	High	Medium	Low	Low
10	High	Medium	Medium	Low
15	High	Medium	Medium	Low

^{*} Thickness (H) of the Seed Layer Relative to Its Critical Thickness (T_{crit}).

Ittle. SEMICONDUCTOR HETEROSTRUCTURES
HAVING REDUCED DISLOCATION PILE-UPS AND
RELATED METHODS
Inventors: Leitz et al.
Express Mail Label No. EV192308504US
Atty Docket No.: ASC-058B
Attorney for Applicants: Mark L. Beloborodov
Sheet 4 of 6

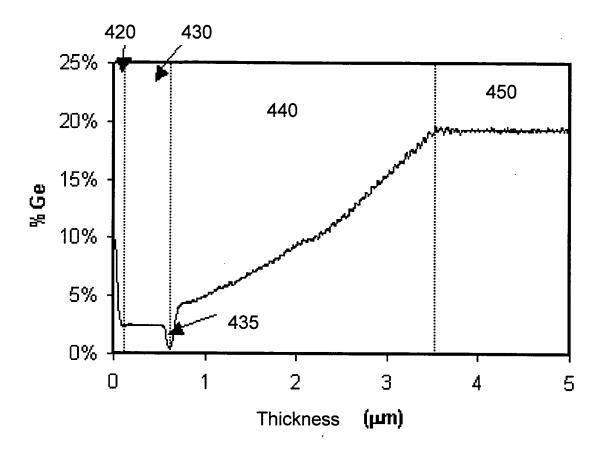


FIG. 4

HAVING REDUCED DISLOCATION PILE-UPS AND RELATED METHODS Inventors: Leitz et al. Express Mail Label No. EV192308504US Atty Docket No.: ASC-058B Attorney for Applicants: Mark L. Beloborodov Sheet 5 of 6

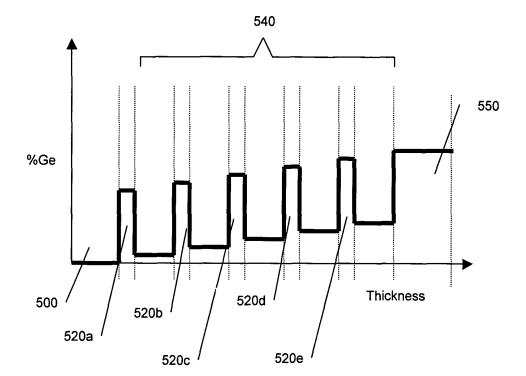


FIG. 5

HAVING REDUCED DISLOCATION PILE-UPS AND RELATED METHODS
Inventors: Leitz et al.
Express Mail Label No. EV192308504US
Atty Docket No.: ASC-058B
Attorney for Applicants: Mark L. Beloborodov
Sheet 6 of 6

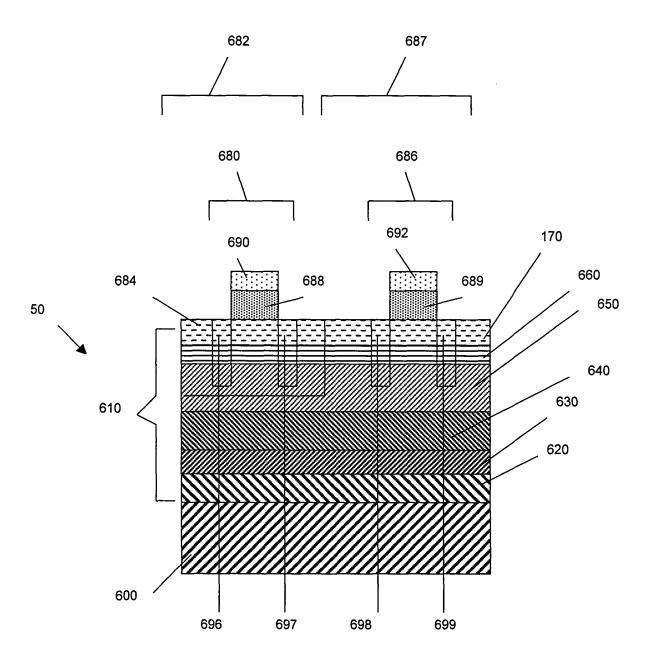


FIG. 6